



W005 THRU W10

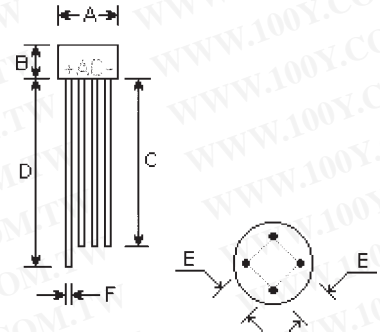
SINGLE-PHASE SILICON BRIDGE
Reverse Voltage - 50 to 1000 Volts
Forward Current - 1.5 Amperes

Features

- Surge overload rating - 50 amperes peak
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- Mounting Position: Any

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

WO



DIM	DIMENSIONS				Note
	inches		mm		
	Min.	Max.	Min.	Max.	
A	0.355	0.395	9.0	10.0	φ
B	0.265	0.305	6.73	7.75	
C	1.20	-	30.5	-	
D	1.27	-	32.3	-	
E	0.180	0.220	4.6	5.6	
F	0.028	0.032	0.71	0.81	φ

Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase, half wave, 60Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

	Symbols	W005	W01	W02	W04	W06	W08	W10	Units
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	Volts
Maximum average forward rectified current $T_A=25^\circ\text{C}$	$I_{(AV)}$	1.5							Amps
Peak forward surge current, 8.3mS single half sine-wave superimposed on rated load	I_{FSM}	50.0							Amps
1 $\frac{1}{2}$ Rating for fusing (t<8.35ms)	I^2t	5.0							A 2t
Maximum forward voltage drop per element at 1.0A peak	V_F	1.0							Volt
Maximum DC reverse current at rated DC blocking voltage per element $T_A=25^\circ\text{C}$ $T_A=100^\circ\text{C}$	I_R	10.0 1.0							μA mA
Operating temperature range	T_J	-55 to +125							°C
Storage temperature range	T_{STG}	-55 to +150							°C

RATINGS AND CHARACTERISTIC CURVES

Fig. 1 — MAXIMUM FORWARD SURGE CURRENT

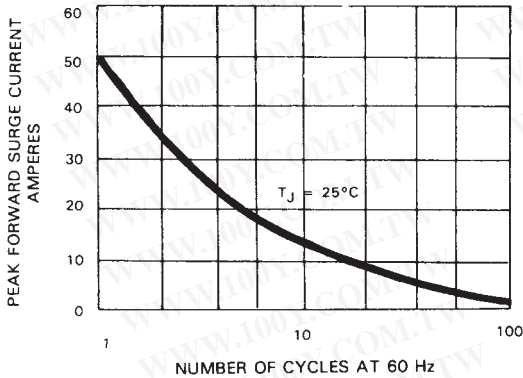


Fig. 2—DERATING CURVE
OUTPUT RECTIFIED CURRENT

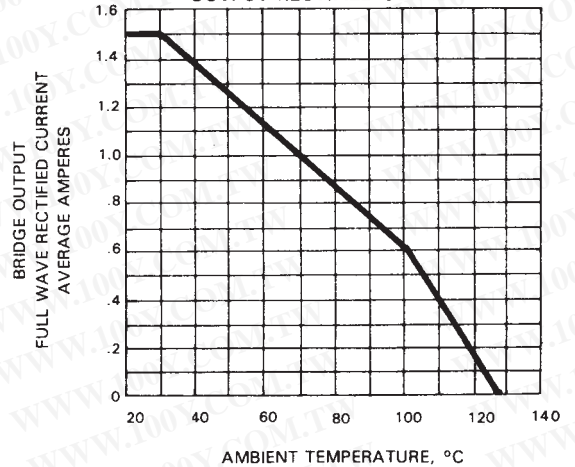


Fig. 3 — TYPICAL FORWARD CHARACTERISTICS

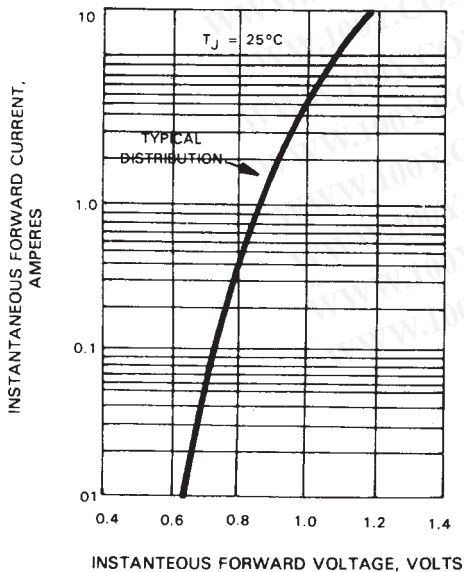


Fig. 4 — TYPICAL REVERSE CHARACTERISTICS

